# Die Attach Film

for Fingerprint sensor

2018. 02.



## [ Fingerprint sensor ]









#### [ Type of Fingerprint Identification Devices ]



(Source: Fingerprint sensor applications and technologies – Consumer market focus, January 2017, Yole Développement)



#### [ i-Phone vs Galaxy for Fingerprint sensor ]

## Fig. 44: 2013 Apple's fingerprint "SiP" vs 2013 Synaptic's fingerprint sensor

SiP is more area efficient and cost efficient per area

	Authentic fingerprint sensor	Synaptics fingerprint sensor
Technology	Capacitive	Capacitive
Туре	Area	Swipe
Cost	Higher (1.5x~2x of Swipe)	Lower
ASP (USD)	8	Less than 5
Die Area	40mm^2	14mm^2
Package Area	121mm^2	52mm^2
Unlock	Touch-based	Swipe-based
Accuracy	High	Low
Speed	Low	High
User-friendly	High	Low
Packaging Technology	SIP from ASE	
Cmartnhana rannaantar	iPhono	
Smartphone representer	IPnone	Samsung Galaxy, HTC One Max
Package area to die area ratio	Зх	3.5x~4x
ASP per package area (use SiP as 1x)	1x	0.9x~1.4x

Source: Chipworks, FingerChip, Nomura research



# [ The Process of Fingerprint sensor ] 1. Wafer 2. back grind 3. Wafer saw 4. Die attach 5. Plasma cleaning 9. SMT with FPCB 6. Wire bonding 7. Mold 8. Package saw **10.** Color Coating 11. Glass Mount 12. Cap Mount **13. Module Test** or Hard coating means the process is made in Foundry, 1. 2. means the process is made in OSAT companies, 3. means the process is made in Module companies. (Source : Nomura Research)

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#### [ Business relationship ]





Hard coating

Bezel attach

material

EMC

#### [Fingerprint sensor assembly]











## [ Protective Cover - Coating Type ]

	Sapphire Glass	Tempered Glass	Crystal Ceramic	UV	
Shape					
Raw materials	Sapphire Glass	Tempered Glass	Composite Ceramic	Resin	
Hardness	***	***	**	★☆	
Glossy	***	***	**☆	**	
Thickness	★ 260,⊭m	★★ 60~70 (About 1/4 of Sapphire)	★★★ 20~30/m (About 1/7 of Sapphire)	★★★ 20~30,40m (About 1/7 of Sapphire)	
Cost	★ About USD1.2 (Based on 260um)	★★☆ About 1/2 of Sapphire	★★★ About 1/4 of Sapphire	★★★ About 1/5 of Sapphire	
Characteristic	Only specific IC for thickness issue / Patent issue	Various ICs available in thin thickness	Simple Process	Simple Process	
Commercialization	In production (Apple)	2H15	1H15	In production	

## Various coating technologies secured: tempered glass, crystal ceramic, UV

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# **Application : Chip to Sub**



#### [ Application : DAF For Fingerprint sensor assembly ]

Type-2: Glass replaced with hard coating on top of EMC



#### [Normal Process(All-in-One)]



Through DAF application, semiconductor packaging companies can get a 1-step process reducing benefit and overcome the weakness(\*) of paste attach process.

#### **Conventional(Paste) Process**



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#### [ Structure & Process(All-in-One) ]



#### All-in-One type(DAF-Dicing film)

DAF is consist of 4 layers including die attach film(DAF) layer. And DAF layer has circle shape to fit for ring frame and wafer attachment.

#### **DAF Structure**



#### **DAF Shape**



#### [ DAF Properties (All-in-One) ]



AMC checks and controls other properties even though not included in specification.



Appearance Tape colo Tape thick	ITEM				
Appearance Tape colo Tape thick	ř.				
Tape thick			milky	y white	
	iness		16	38µm	
Base film			Polyalefi	in / 100µr	
DAF			2	Oym	
Adhesive	Adhesive layer				
Protective	film		PET	/ 38µm	
Properties Peel stre	ngth of Dicing Film	before UV	1.23 /	N/25nn <sup>1)</sup>	
		after UV	0.13	N/25nm	
Peel stre	ngth of DCF/DAF	before UV	0.68	N/25nn	
		after UV	0.11	N/25nn	
Adhesion	Adhesion strength				
Wafer mo	Wafer mounting temperature				
UV exposu	UV exposure				
Cure start	ing temperature		13	90°C	
Die bondin	Die bonding temperature				
Curing co	ndition		180°C	(60min)	
Decompos	Decomposition Temperature				
DAF elong	DAF elongation				
CTE		below Tg	210p	pm/*C	
		above Tg	260p	pm/*C	
Tg.			21	0°C	
Bastic mo	dulus		6MPa (a	at 250°C)	
Enthalpy			45	5J/g	
Volume re	sistivity			R/cm	
Water abs	orption (85°C/85R H	6/48Hrs)	0.4	4 96	
RoHS			No	thing	
Ion impur	ty (Na+, K+ Q_ )		< 1	0ppm	
Dicing file	n elongation		MD :	350%	
			TD :	700%	

#### [DAF Properties (All-in-One)]

Compared with other DAF player's Die Shear Strength reliability in harsh condition(MRT( \* )), AMC product shows the best performance.

#### **10**/m DAF layer Die Shear Strength comparison test



	ES-229 Series	Player 1	Player 2
0hr	39.5	35.8	28.9
12hr	32.8	25.9	15.6
24hr	27.8	22.1	11.3

(\*) Player 1, 2 : Korean major domestic players



(Unit: MPa)



## [ Evaluation Results ]



#### **Test Product Model**

Dummy wafer

#### **Test Parameter**

Sp	oindle RPM	Feed Speed	Blade Height	Dicing Blade	Cut Method
Z1	45,000	80 mm/s	155um	ZH05-SD3500-N1-CC	Chara Cut
Z2	45,000	80 mm/s	70um	ZH05-SD3500-N1-BB	Step Cut

#### **Test Result**

Sample	Wafer Thick.	Corner burr(%)	Side burr(%)	Bleed(%)
ES-229	50um	0.0	2.7	2.7
Competitor A (Model A)	50um	0.0	42.4	36.3



#### [ Evaluation Results ]

#### Test Image

\* Test condition : After UV

	Тор	Corner	Side	Bleed
ES-229				
Competitor A (Model A)				

#### Back grind / wafer sawing Process Quality Control Data

Item	S/S	Spec	1	2	3	4	5	6	7	8	9	10	Min.	Max.	Avg.	Result
Kerf	Z1 : 8Line	Max	32	35	32	36	34	35	37	32	32	33	32.0	37.0	33.8	Accept
Width	Z2:8Line	60um	30	32	31	32	31	33	31	35	36	35	30.0	36.0	32.6	Accept



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#### [ Evaluation Results - Workability Test Results ]

Item	Die	S/S	Spec.	1	2	3	4	5	6	7	8	9	10	Min.	Max.	Avg.	Result
	1 at Dia	X : 10Unit		13	16	18	10	16	11	10	15	13	13	10	18	14	Accept
Die	IST DIE	Y:10Unit		8	13	10	13	11	11	13	14	13	12	8	14	12	Accept
Position		X : 10Unit	± 50um	11	8	8	10	6	11	10	11	11	13	6	13	10	Accept
	2na Die	Y:10Unit		13	11	12	10	11	14	15	17	13	11	10	17	13	Accept

## Back grind / wafer sawing Process Quality Control Data

#### **Chip to Chip Void**

	C-Scan	Result
		Accept

#### [ Evaluation Results - Reliability Test Results ]



#### **Pre-con Test**



T/C	-55~125℃, 5cycle
Bake	125℃ 24Hrs
T/H	85℃/85% 96Hrs
Reflow	Peak 260℃, 3 cycle



# Application : EMC to Protective Cover



#### [ Application : EMC to Protective Cover ]

# [ EMC and Protective cover attaching method under development ]



#### Advantage

- JEDEC Level 2
- High adhesive strength
- Various colors

#### [ Color film attachment method ]



#### **Cut Process**



\* Heat block depend on customer.

#### [Structure & Product ]



#### > Only DAF type

DAF is consist of 3 layers including die attach film(DAF) layer.

#### **DAF Structure**



#### **Product line**

- AWD1 series
- AWD4 series

#### [DAF Properties (Only DAF)]



CAMC

AMC checks and controls other properties even though not included in specification.



#### Technical Data Sheet

#### 1. MODEL : AWD4-5 series(Under Development R&D)

#### 2. FEATURE

- JEDEC Level 2
- Thermal curing type, high adhesive strength

#### 3. SPECIFICATION

	ITEM		AWD4-5
Appearance	Structure		Primer film
	Type of Adhesive film	Thermosetting type	
	Thickness(µn)	5±3	
Property	Glass transition temperature("C)		188.3
	5% weight loss temperature("C)	-	
		-55°C	•
		010	-
	Bastic modulus(MPa)	50°c	-
		100°C	215
		200°c	37.1
		250°C	29.8
	CTE(ppm/'C)		148
		Q:	•
	Ionic impurity(ppm)	K+	-
		Na+	•
	Water absorption(85°C /85% RH/24h,	w <b>t%</b> )	

#### 4. Expiration time

12 months after production (under S\*C) 1 months after opening (under RT) Cure condition : 1hr 30min at 80~180°c

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#### [ DAF Properties ( Only DAF ) - reaction ratio ]



#### AWD1 & AWD4 reaction ratio



Measure reaction ratio using the cured DAF at changing the temperature linearly R.T. to  $300^{\circ}$ C



% Curing Temp. : 150  $^\circ \!\!\! \mathbb{C}$ 



#### [ DAF Properties ( Only DAF ) - Die Shear Test ]

#### AWD1 Die Shear Test



	Unit	Competitor	AWD1
① after die bonding		0.8	1.1
② 85°C,85%, 0hr(after cure)	MPa	31.7	50.8
③ 85℃,85%, 24hr(after cure)		35.4	36.2

#### Process & condition

- ① wafer dicing → die bonding(1kgf, 10sec, 75 °C) → die shear test
- ② wafer dicing → die bonding(1kgf, 10sec, 75 °C) → full cure(@ 1hr at 150 °C) → die shear test
- ③ wafer dicing → die bonding(1kgf, 10sec, 75 °C) → full cure(@ 1hr at 150 °C)
  - $\rightarrow$  Thermo-hydrostatic(85%, 85°C, 24hr)  $\rightarrow$  die shear test



# **Thank You!**